

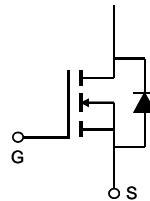
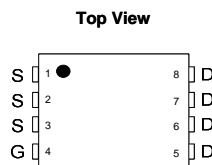
### General Description

The AON6232 uses trench MOSFET technology that is uniquely optimized to provide the most efficient high frequency switching performance. Power losses are minimized due to an extremely low combination of  $R_{DS(ON)}$  and  $C_{rss}$ . In addition, switching behavior is well controlled with a "Schottky style" soft recovery body diode.

### Product Summary

$V_{DS}$	40V
$I_D$ (at $V_{GS}=10V$ )	85A
$R_{DS(ON)}$ (at $V_{GS}=10V$ )	< 2.5m $\Omega$
$R_{DS(ON)}$ (at $V_{GS} = 4.5V$ )	< 3.6m $\Omega$

100% UIS Tested  
100%  $R_g$  Tested



#### Absolute Maximum Ratings $T_A=25^\circ\text{C}$ unless otherwise noted

Parameter	Symbol	Maximum	Units
Drain-Source Voltage	$V_{DS}$	40	V
Gate-Source Voltage	$V_{GS}$	$\pm 20$	V
Continuous Drain Current <sup>G</sup>	$I_D$	$T_C=25^\circ\text{C}$	85
		$T_C=100^\circ\text{C}$	67
Pulsed Drain Current <sup>C</sup>	$I_{DM}$	260	A
Continuous Drain Current	$I_{DSM}$	$T_A=25^\circ\text{C}$	22
		$T_A=70^\circ\text{C}$	17
Avalanche Current <sup>C</sup>	$I_{AS}, I_{AR}$	60	A
Avalanche energy $L=0.1\text{mH}$ <sup>C</sup>	$E_{AS}, E_{AR}$	180	mJ
Power Dissipation <sup>B</sup>	$P_D$	$T_C=25^\circ\text{C}$	83
		$T_C=100^\circ\text{C}$	33
Power Dissipation <sup>A</sup>	$P_{DSM}$	$T_A=25^\circ\text{C}$	2.3
		$T_A=70^\circ\text{C}$	1.4
Junction and Storage Temperature Range	$T_J, T_{STG}$	-55 to 150	$^\circ\text{C}$

#### Thermal Characteristics

Parameter	Symbol	Typ	Max	Units
Maximum Junction-to-Ambient <sup>A</sup>	$R_{\theta JA}$	$t \leq 10\text{s}$	14	$^\circ\text{C}/\text{W}$
Maximum Junction-to-Ambient <sup>A D</sup>		Steady-State	40	$^\circ\text{C}/\text{W}$
Maximum Junction-to-Case	$R_{\theta JC}$	1.1	1.5	$^\circ\text{C}/\text{W}$







### TYPICAL ELECTRICAL AND THERMAL CHARACTERISTICS

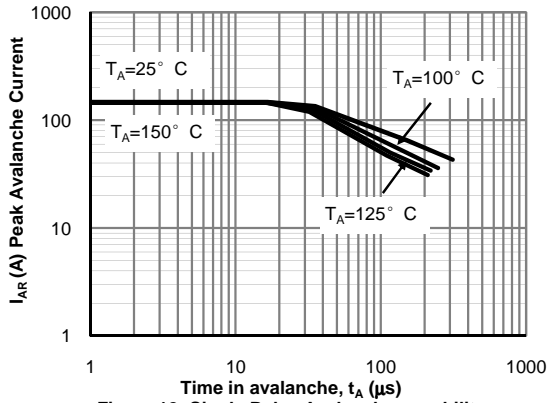


Figure 12: Single Pulse Avalanche capability (Note C)

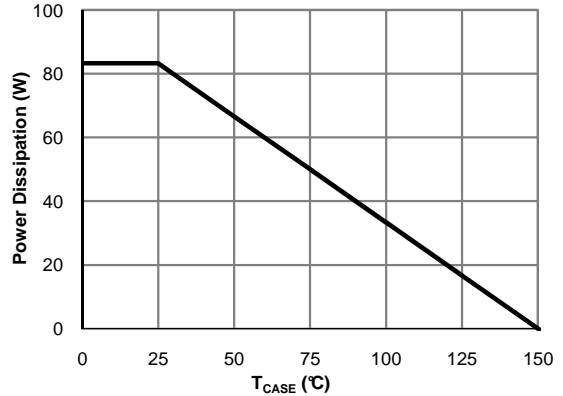


Figure 13: Power De-rating (Note F)

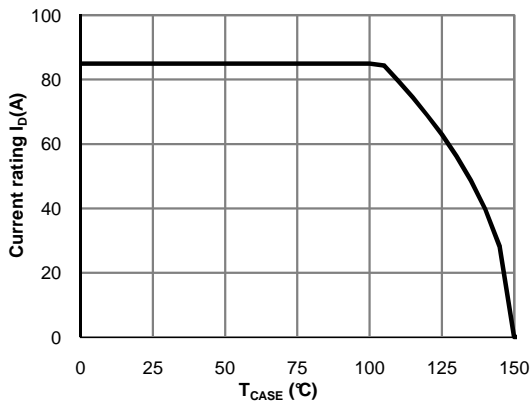


Figure 14: Current De-rating (Note F)

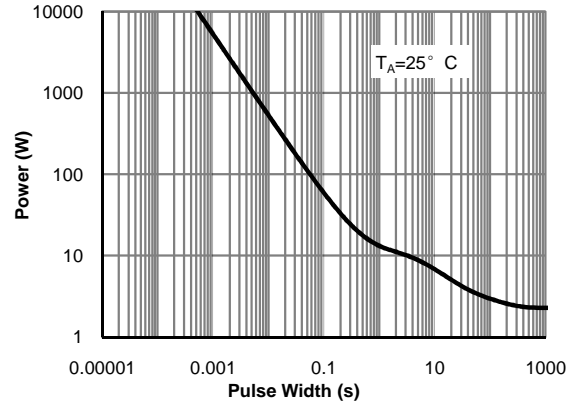


Figure 15: Single Pulse Power Rating Junction-to-Ambient (Note H)

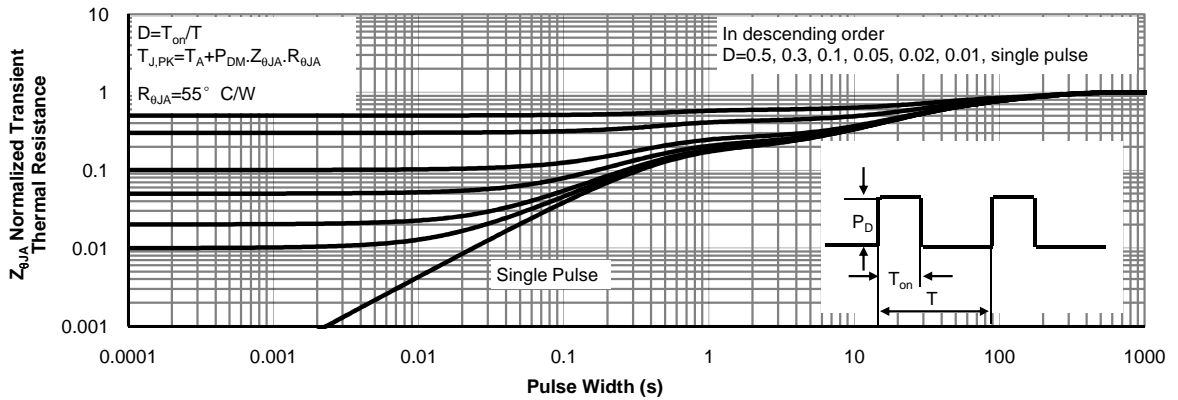
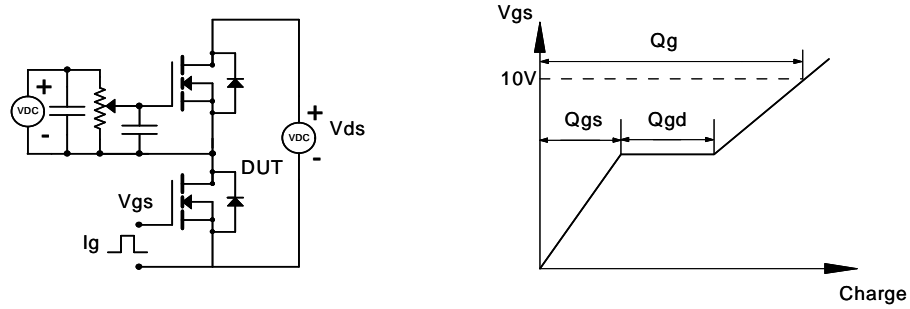
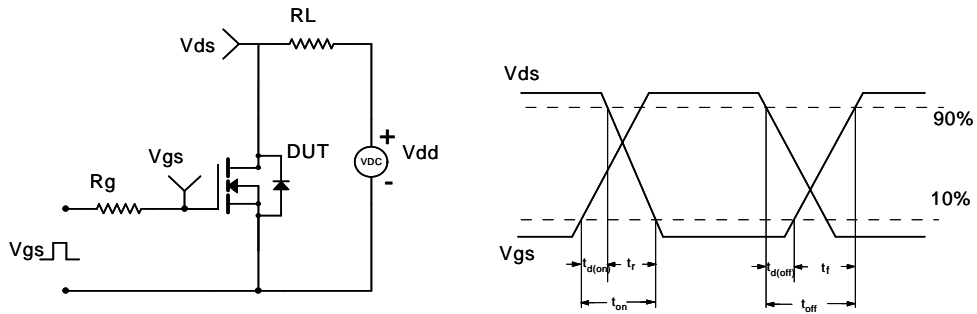


Figure 16: Normalized Maximum Transient Thermal Impedance (Note H)

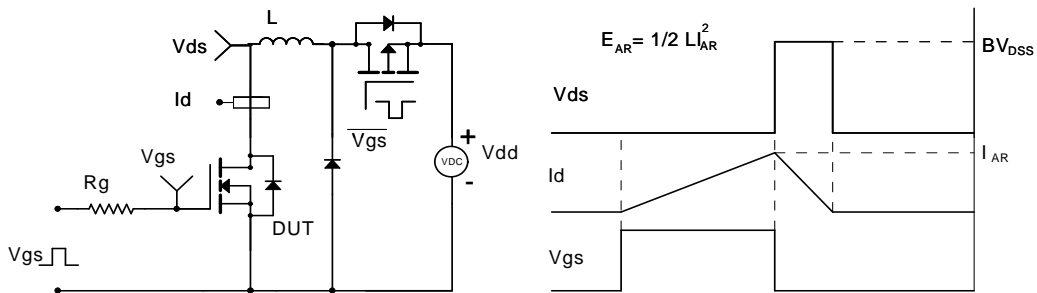
Gate Charge Test Circuit & Waveform



Resistive Switching Test Circuit & Waveforms



Unclamped Inductive Switching (UIS) Test Circuit & Waveforms



Diode Recovery Test Circuit & Waveforms

